

PowerMOS transistor

Fast recovery diode FET

BUK655-500B

GENERAL DESCRIPTION

N-channel enhancement mode field-effect power transistor in a plastic envelope.
FREDFET with fast recovery reverse diode, particularly suitable for motor control applications, eg. in full bridge configurations for which faster recovery characteristics simplify design for inductive loads.

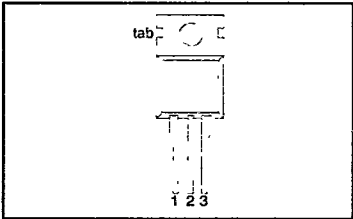
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DS}	Drain-source voltage	500	V
I_D	Drain current (DC)	5.3	A
P_{tot}	Total power dissipation	100	W
$R_{DS(ON)}$	Drain-source on-state resistance	1.5	Ω
t_r	Diode reverse recovery time	250	ns

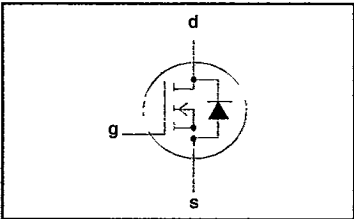
PINNING - TO220AB

PIN	DESCRIPTION
1	gate
2	drain
3	source
tab	drain

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Drain-source voltage	-	-	500	V
V_{DGR}	Drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	500	V
$\pm V_{GS}$	Gate-source voltage	-	-	30	V
I_D	Drain current (DC)	$T_{mb} = 25\text{ }^\circ\text{C}$	-	5.3	A
I_D	Drain current (DC)	$T_{mb} = 100\text{ }^\circ\text{C}$	-	3.3	A
I_{DM}	Drain current (pulse peak value)	$T_{mb} = 25\text{ }^\circ\text{C}$	-	21	A
P_{tot}	Total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$	-	100	W
T_{stg}	Storage temperature	-	- 55	150	$^\circ\text{C}$
T_j	Junction Temperature	-	-	150	$^\circ\text{C}$

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\,j\,mb}$	Thermal resistance junction to mounting base		-	-	1.25	K/W
$R_{th\,j\,a}$	Thermal resistance junction to ambient		-	60	-	K/W

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STATIC CHARACTERISTICS $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 0.25\text{ mA}$	500	-	-	V
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS} = V_{GS}; I_D = 1\text{ mA}$	2.1	3.0	4.0	V
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 500\text{ V}; V_{GS} = 0\text{ V}; T_J = 25\text{ }^{\circ}\text{C}$	-	2	20	μA
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 500\text{ V}; V_{GS} = 0\text{ V}; T_J = 125\text{ }^{\circ}\text{C}$	-	0.1	1.0	mA
I_{GSS}	Gate source leakage current	$V_{GS} = \pm 30\text{ V}; V_{DS} = 0\text{ V}$	-	10	100	nA
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 2.5\text{ A}$	-	1.4	1.5	Ω

DYNAMIC CHARACTERISTICS $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	$V_{DS} = 25\text{ V}; I_D = 2.5\text{ A}$	2.3	3.1	-	S
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$	-	750	1000	pF
C_{oss}	Output capacitance		-	90	140	pF
C_{res}	Feedback capacitance		-	40	70	pF
t_{don}	Turn-on delay time	$V_{DD} = 30\text{ V}; I_D = 2.6\text{ A};$	-	10	45	ns
t_r	Turn-on rise time	$V_{GS} = 10\text{ V}; R_{GS} = 50\text{ }\Omega;$	-	45	60	ns
t_{doff}	Turn-off delay time	$R_{gen} = 50\text{ }\Omega$	-	100	140	ns
t_f	Turn-off fall time		-	40	65	ns
L_d	Internal drain inductance	Measured from contact screw on tab to centre of die	-	3.5	-	nH
L_d	Internal drain inductance	Measured from drain lead 6 mm from package to centre of die	-	4.5	-	nH
L_s	Internal source inductance	Measured from source lead 6 mm from package to source bond pad	-	7.5	-	nH

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current	-	-	-	5.7	A
I_{DRM}	Pulsed reverse drain current	-	-	-	23	A
V_{SD}	Diode forward voltage	$I_F = 5.7\text{ A}; V_{GS} = 0\text{ V}$	-	1.1	1.5	V
t_{rr}	Reverse recovery time	$I_F = 5.7\text{ A}; T_J = 25\text{ }^{\circ}\text{C}$	-	180	250	ns
		$-di_F/dt = 100\text{ A}/\mu\text{s}; T_J = 125\text{ }^{\circ}\text{C}$	-	220	300	ns
Q_{rr}	Reverse recovery charge	$I_F = 5.7\text{ A}; T_J = 25\text{ }^{\circ}\text{C}$	-	0.65	1.2	μC
		$T_J = 125\text{ }^{\circ}\text{C}$	-	2.6	5.0	μC
I_{rm}	Reverse recovery current	$V_{GS} = 0\text{ V}; V_R = 100\text{ V}; T_J = 125\text{ }^{\circ}\text{C}$	-	15	-	A

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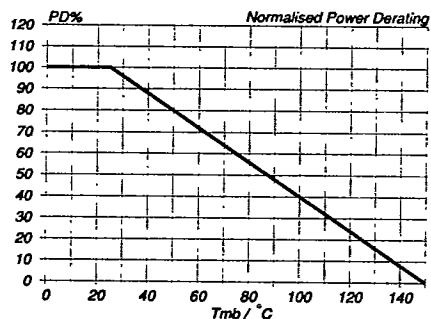


Fig. 1. Normalised power dissipation.
 $PD\% = 100 \cdot P_D / P_{D 25^\circ C} = f(T_{mb})$

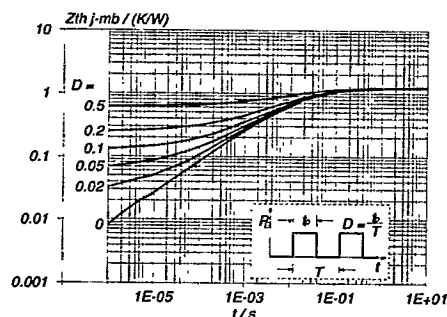


Fig. 4. Transient thermal impedance.
 $Z_{th j-mb} = f(t)$; parameter $D = t_j / T$

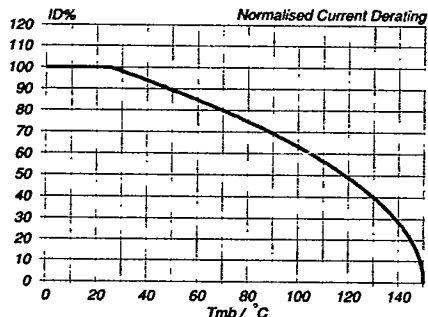


Fig. 2. Normalised continuous drain current.
 $ID\% = 100 \cdot I_D / I_{D 25^\circ C} = f(T_{mb})$; conditions: $V_{GS} \geq 10 \text{ V}$

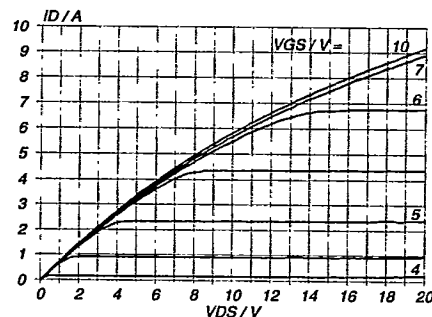


Fig. 5. Typical output characteristics, $T_j = 25^\circ C$.
 $I_D = f(V_{DS})$; parameter V_{GS}

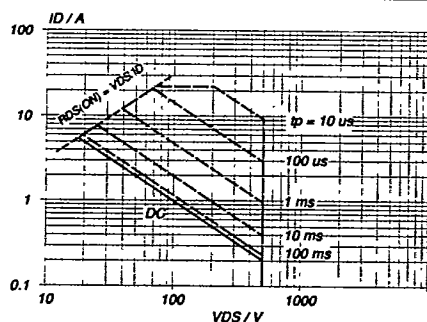


Fig. 3. Safe operating area. $T_{mb} = 25^\circ C$
 I_D & $I_{DM} = f(V_{DS})$; I_{DM} single pulse; parameter t_p

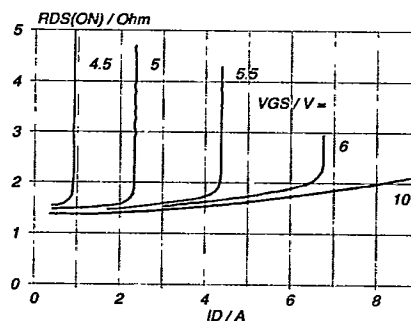


Fig. 6. Typical on-state resistance, $T_j = 25^\circ C$.
 $R_{DS(ON)} = f(I_D)$; parameter V_{GS}

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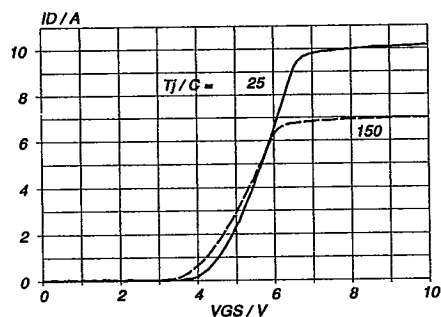


Fig. 7. Typical transfer characteristics.
 $I_D = f(V_{GS})$; conditions: $V_{DS} = 25\text{ V}$; parameter T_j

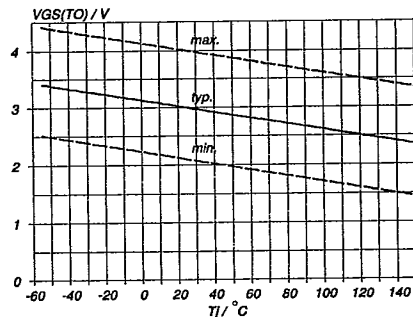


Fig. 10. Gate threshold voltage.
 $V_{GS(T0)} = f(T_j)$; conditions: $I_D = 1\text{ mA}$; $V_{DS} = V_{GS}$

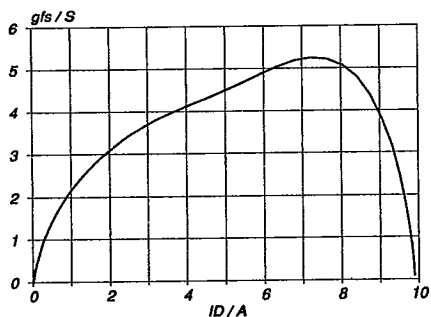


Fig. 8. Typical transconductance, $T_j = 25\text{ °C}$.
 $g_{fs} = f(I_D)$; conditions: $V_{DS} = 25\text{ V}$

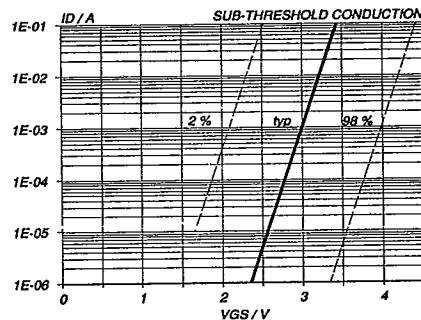


Fig. 11. Sub-threshold drain current.
 $I_D = f(V_{GS})$; conditions: $T_j = 25\text{ °C}$; $V_{DS} = V_{GS}$

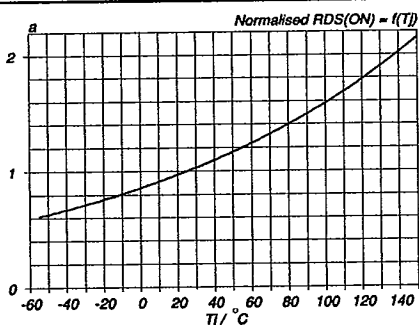


Fig. 9. Normalised drain-source on-state resistance.
 $a = R_{DS(ON)}/R_{DS(ON)25\text{ °C}} = f(T_j)$; $I_D = 2.5\text{ A}$; $V_{GS} = 10\text{ V}$

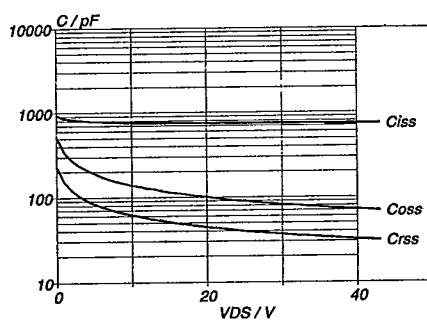


Fig. 12. Typical capacitances, C_{iss} , C_{oss} , C_{rss} .
 $C = f(V_{DS})$; conditions: $V_{GS} = 0\text{ V}$; $f = 1\text{ MHz}$

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